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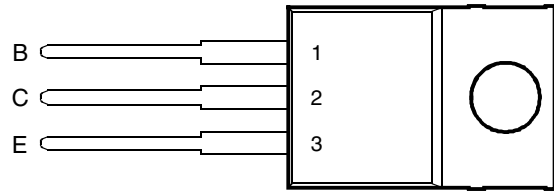
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- Designed for Complementary Use with BD895, BD897, BD899 and BD901
- 70 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3A

TO-220 PACKAGE
(TOP VIEW)



This series is obsolete and not recommended for new designs.

Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BD896	V_{CB0}	-45	V
	BD898		-60	
	BD900		-80	
	BD902		-100	
Collector-emitter voltage ($I_B = 0$)	BD896	V_{CE0}	-45	V
	BD898		-60	
	BD900		-80	
	BD902		-100	
Emitter-base voltage		V_{EB0}	-5	V
Continuous collector current		I_C	-8	A
Continuous base current		I_B	-0.3	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)		P_{tot}	70	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 2)		P_{tot}	2	W
Operating free-air temperature range		T_A	-65 to +150	°C
Operating junction temperature range		T_j	-65 to +150	°C
Storage temperature range		T_{stg}	-65 to +150	°C

NOTES: 1. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
2. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.

PRODUCT INFORMATION

AUGUST 1993 - REVISED SEPTEMBER 2002
Specifications are subject to change without notice.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$ Collector-emitter breakdown voltage	$I_C = -100 \text{ mA}$ $I_B = 0$ (see Note 3)	BD896 BD898 BD900 BD902	-45 -60 -80 -100		V
I_{CEO} Collector-emitter cut-off current	$V_{CE} = -30 \text{ V}$ $I_B = 0$ $V_{CE} = -30 \text{ V}$ $I_B = 0$ $V_{CE} = -40 \text{ V}$ $I_B = 0$ $V_{CE} = -50 \text{ V}$ $I_B = 0$	BD896 BD898 BD900 BD902		-0.5 -0.5 -0.5 -0.5	mA
I_{CBO} Collector cut-off current	$V_{CB} = -45 \text{ V}$ $I_E = 0$ $V_{CB} = -60 \text{ V}$ $I_E = 0$ $V_{CB} = -80 \text{ V}$ $I_E = 0$ $V_{CB} = -100 \text{ V}$ $I_E = 0$ $V_{CB} = -45 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ $V_{CB} = -60 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ $V_{CB} = -80 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$ $V_{CB} = -100 \text{ V}$ $I_E = 0$ $T_C = 100^\circ\text{C}$	BD896 BD898 BD900 BD902 BD896 BD898 BD900 BD902		-0.2 -0.2 -0.2 -0.2 -2 -2 -2 -2	mA
I_{EBO} Emitter cut-off current	$V_{EB} = -5 \text{ V}$ $I_C = 0$ (see Notes 3 and 4)			-2	mA
h_{FE} Forward current transfer ratio	$V_{CE} = -3 \text{ V}$ $I_C = -3 \text{ A}$ (see Notes 3 and 4)		750		
$V_{CE(sat)}$ Collector-emitter saturation voltage	$I_B = -12 \text{ mA}$ $I_C = -3 \text{ A}$ (see Notes 3 and 4)			-2.5	V
$V_{BE(on)}$ Base-emitter voltage	$V_{CE} = -3 \text{ V}$ $I_C = -3 \text{ A}$ (see Notes 3 and 4)			-2.5	V
V_{EC} Parallel diode forward voltage	$I_E = -8 \text{ A}$ $I_B = 0$			-3.5	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

4. These parameters must be measured using voltage sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			1.79	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †	MIN	TYP	MAX	UNIT
t_{on} Turn-on time	$I_C = -3 \text{ A}$ $I_{B(on)} = -12 \text{ mA}$ $I_{B(off)} = 12 \text{ mA}$		1		μs
t_{off} Turn-off time	$V_{BE(off)} = 3.5 \text{ V}$ $R_L = 10 \Omega$ $t_p = 20 \mu\text{s}$, dc $\leq 2\%$		5		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN
VS
COLLECTOR CURRENT

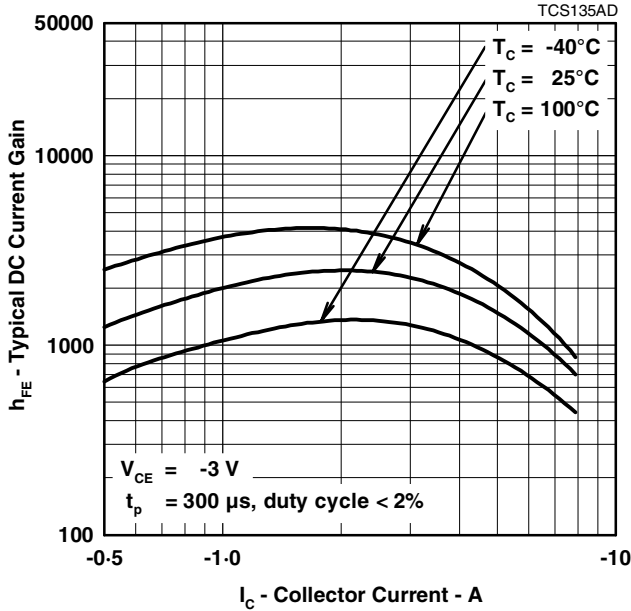


Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

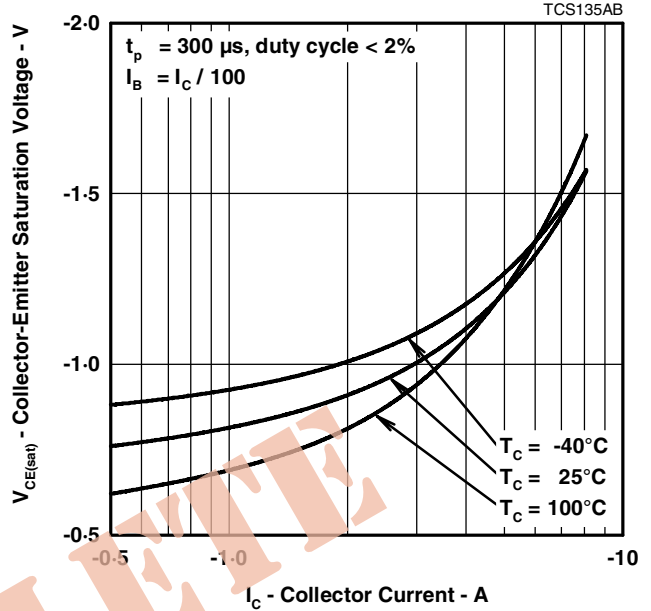


Figure 2.

BASE-EMITTER SATURATION VOLTAGE
VS
COLLECTOR CURRENT

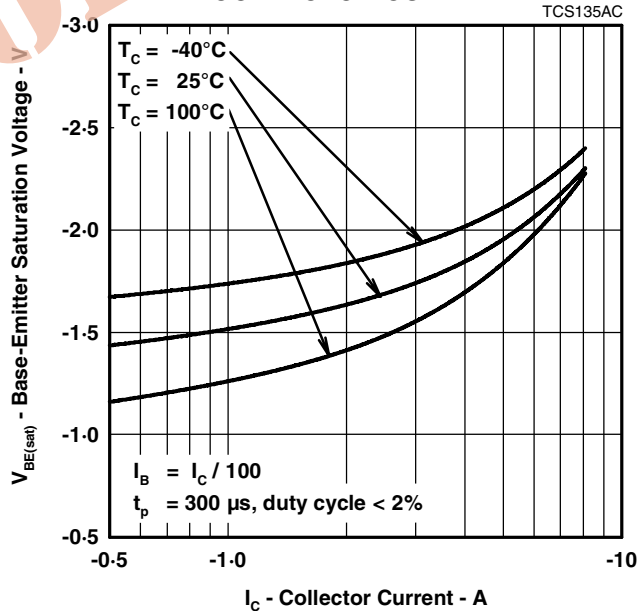


Figure 3.

PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

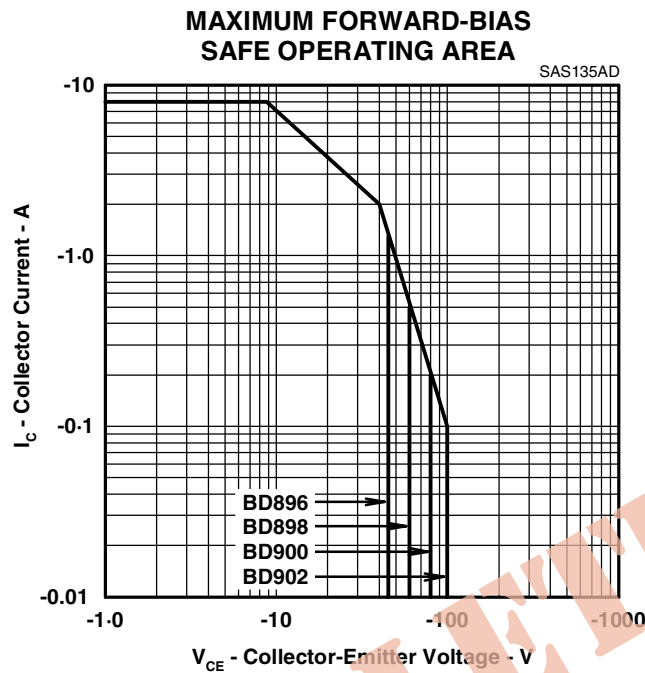


Figure 4.

THERMAL INFORMATION

**MAXIMUM POWER DISSIPATION
vs
CASE TEMPERATURE**

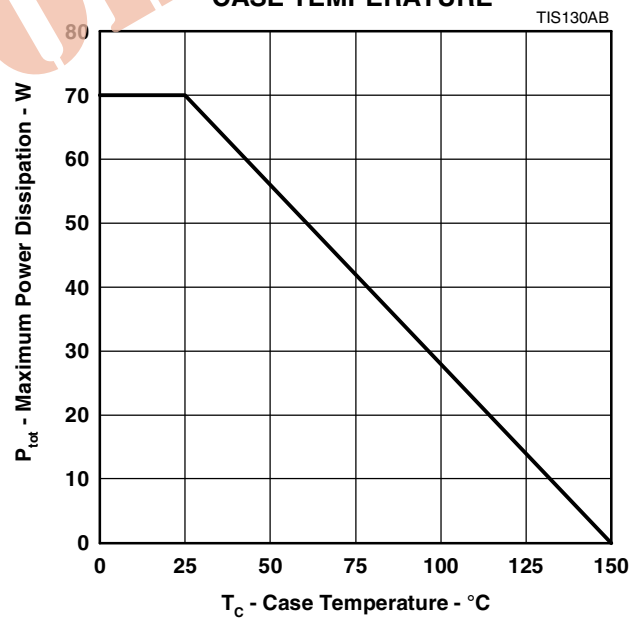


Figure 5.

PRODUCT INFORMATION